

Figures

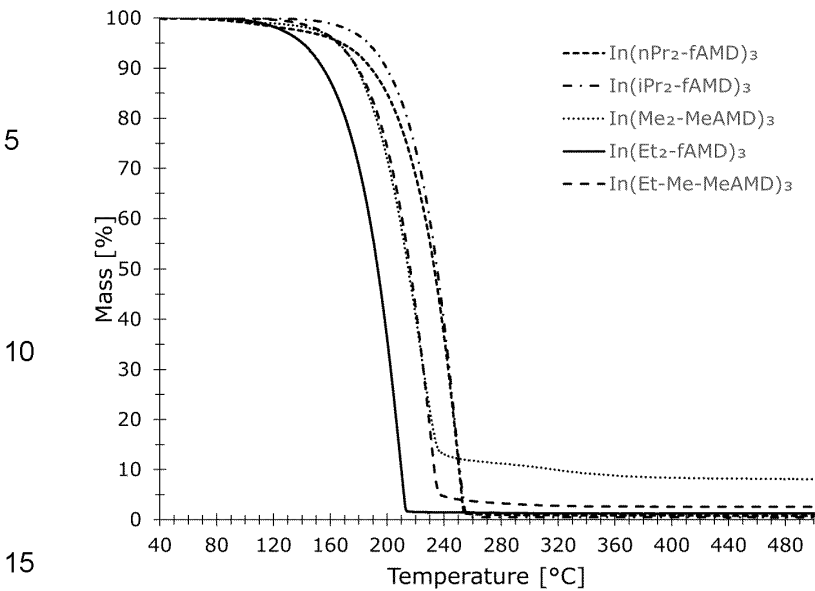


Figure 1. TGA curves of the synthesized In precursors

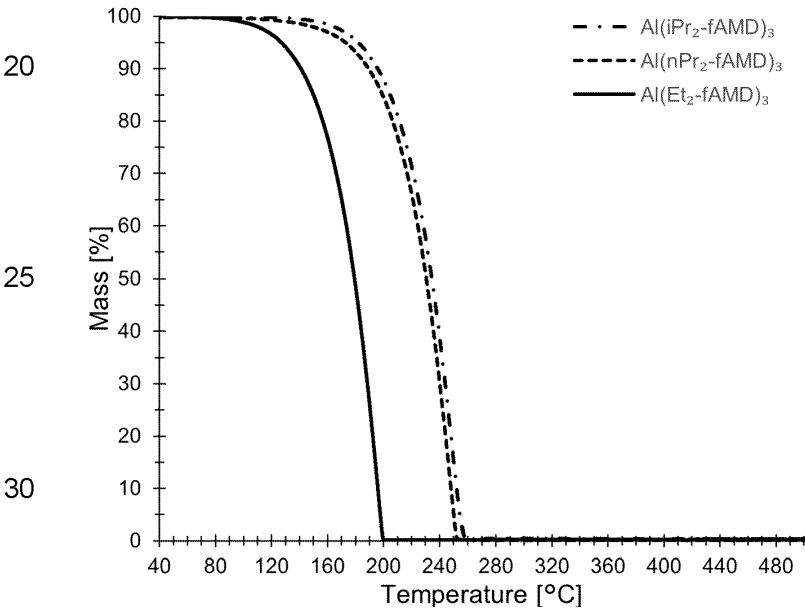


Figure 2. TGA curves of the synthesized Al precursors

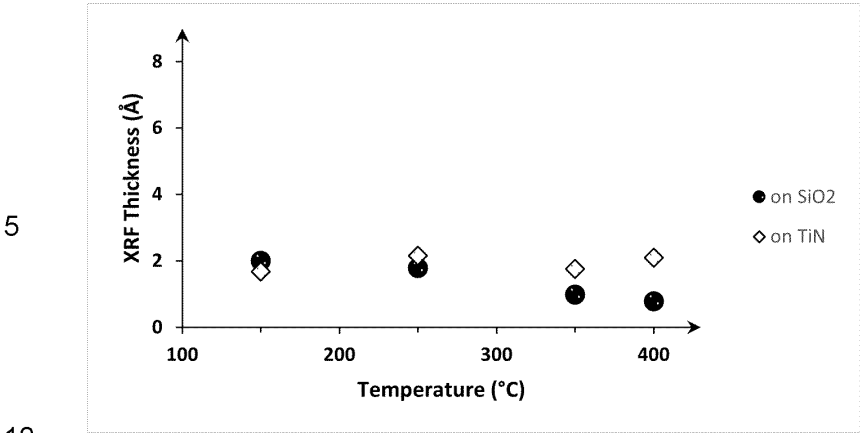


Fig. 3. Thermal decomposition study of $\text{In}(\text{Et}_2\text{-fAMD})_3$ on SiO_2 and TiN .

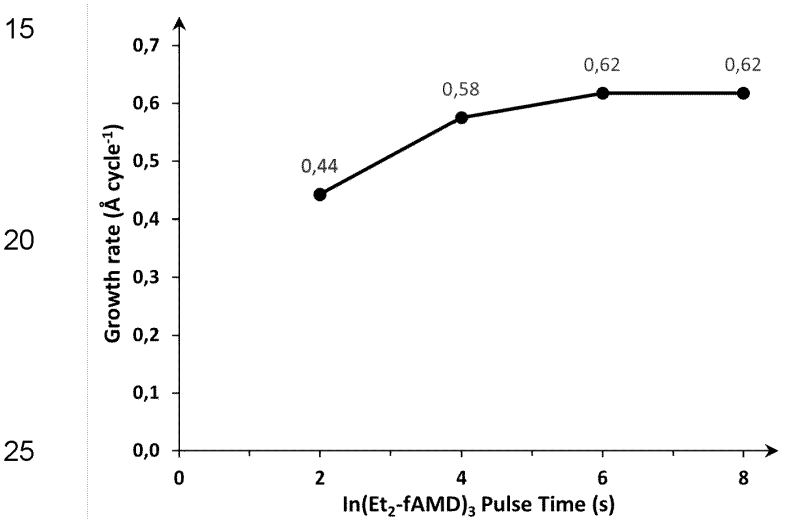


Fig. 4. Saturation study of $\text{In}(\text{Et}_2\text{-fAMD})_3$ with O_3 as co-reactant on SiO_2 at 300°C substrate temperature.

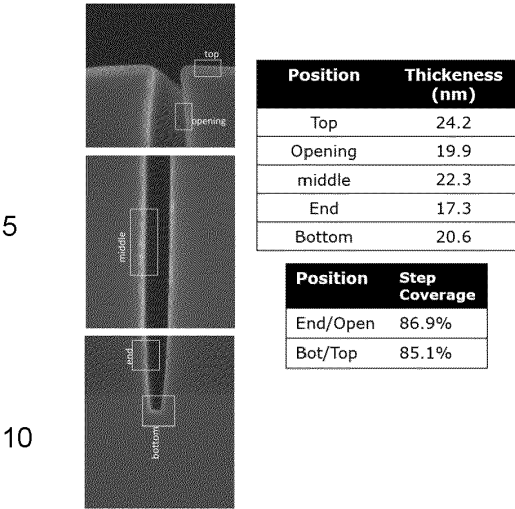


Fig. 5. SEM micrographs of the top, middle and bottom position of a Si (native oxide) trench substrate with an aspect ratio of 17:1, coated by indium oxide from $\text{In}(\text{Et}_2\text{fAMD})_3$ and O_3 at 300 °C and estimated thin film thicknesses (from SEM) at the indicated positions with calculated step coverage values.